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ABSTRACT OF THE DISCLOSURE

SEMICONDUCTOR INTEGRATED CIRCUIT DEVICE AND
METHOD FOR MANUFACTURING THE SAME.

A dynamic random access memory or the like, in
which in order to prevent the breakdown voltage
deterioration of a capacitive element when a TiN film
5 of an electrode material is deposited by the CVD
method over a tantalum film constituting the capacitor
insulating film of the capacitive element, a
passivation film is formed in advance over the surface
of the tantalum oxide film to prevent the tantalum
10 oxide film from contacting with a nitrogen-containing
reducing gas, when the TiN film is deposited over the
tantalum oxide film by the CVD method using a
titanium-containing source gas and the nitrogen-
containing reducing gas.

15. Figure 17



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